

PNP High Voltage Amplifier

This device is designed for high voltage driver applications. Sourced from Process 76.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units | |
|-----------------------------------|--|-------------|-------|--|
| V _{CEO} | Collector-Emitter Voltage | 300 | V | |
| V _{CBO} | Collector-Base Voltage | 300 | V | |
| V _{EBO} | Emitter-Base Voltage | 5.0 | V | |
| l _c | Collector Current - Continuous | 500 | mA | |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C | |

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

| Symbol | Characteristic | Мах | | Units | |
|-----------------------|---|--------|----------|----------|-------|
| | | MPSA92 | *MMBTA92 | **PZTA92 | |
| PD | Total Device Dissipation | 625 | 350 | 1,000 | mW |
| | Derate above 25°C | 5.0 | 2.8 | 8.0 | mW/°C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 83.3 | | | °C/W |
| $R_{	extsf{	heta}JA}$ | Thermal Resistance, Junction to Ambient | 200 | 357 | 125 | °C/W |

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

** Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

PNP High Voltage Amplifier (c

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|-----|-------|-----|
| | | |

| Electrical Characteristics TA = 25°C unless otherwise noted | | | | | | |
|---|--------------------------------------|--|-----|------|-------|--|
| Symbol | Parameter Test Conditions M | | Min | Max | Units | |
| OFF CHA | RACTERISTICS | | | | | |
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage* | $I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$ | 300 | | V | |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | $I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$ | 300 | | V | |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | $I_{\rm E} = 100 \ \mu {\rm A}, \ I_{\rm C} = 0$ | 5.0 | | V | |
| СВО | Collector-Cutoff Current | $V_{CB} = 200 \text{ V}, I_E = 0$ | | 0.25 | μΑ | |
| EBO | Emitter-Cutoff Current | $V_{EB} = 3.0 \text{ V}$. $I_{C} = 0$ | | 0.1 | μA | |

ON CHARACTERISTICS*

| h _{FE} | DC Current Gain | I _C = 1.0 mA, V _{CE} = 10 V | 25 | | |
|----------------------|--------------------------------------|---|----|-----|---|
| | | $I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ | 40 | | |
| | | $I_{C} = 30 \text{ mA}, V_{CE} = 10 \text{ V}$ | 25 | | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | $I_{\rm C} = 20$ mA, $I_{\rm B} = 2.0$ mA | | 0.5 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | $I_{\rm C} = 20$ mA, $I_{\rm B} = 2.0$ mA | | 0.9 | V |

SMALL SIGNAL CHARACTERISTICS

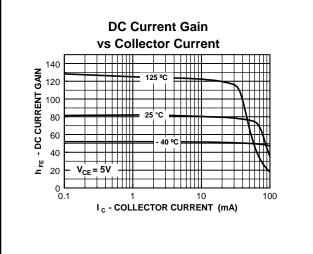
| f⊤ | Current Gain - Bandwidth Product | $I_{C} = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100 MHz | 50 | | MHz |
|-----------------|----------------------------------|--|----|-----|-----|
| C _{cb} | Collector-Base Capacitance | $V_{CB} = 20 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ | | 6.0 | pF |

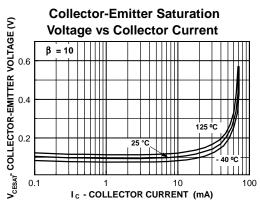
*Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

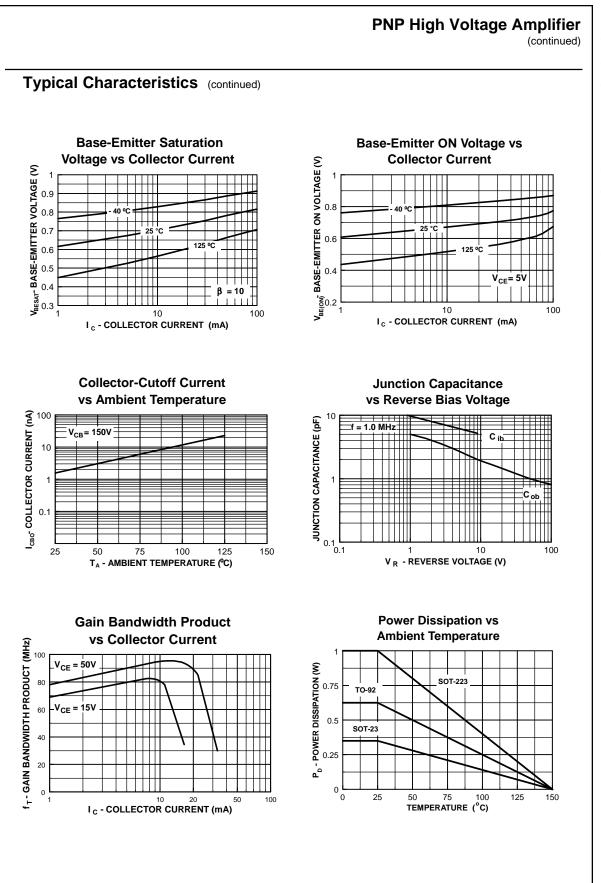
Spice Model

PNP (Is=218.9f Xti=3 Eg=1.11 Vaf=100 Bf=99 Ne=1.307 Ise=218.9f Ikf=.2016 Xtb=1.5 Br=24.67 Nc=2 Isc=0 Ikr=0 Rc=7 Cjc=19.88p Mjc=.4876 Vjc=.75 Fc=.5 Cje=81.49p Mje=.3493 Vje=.75 Tr=516.9p Tf=1.395n Itf=1.5 Vtf=22 Xtf=270 Rb=10)

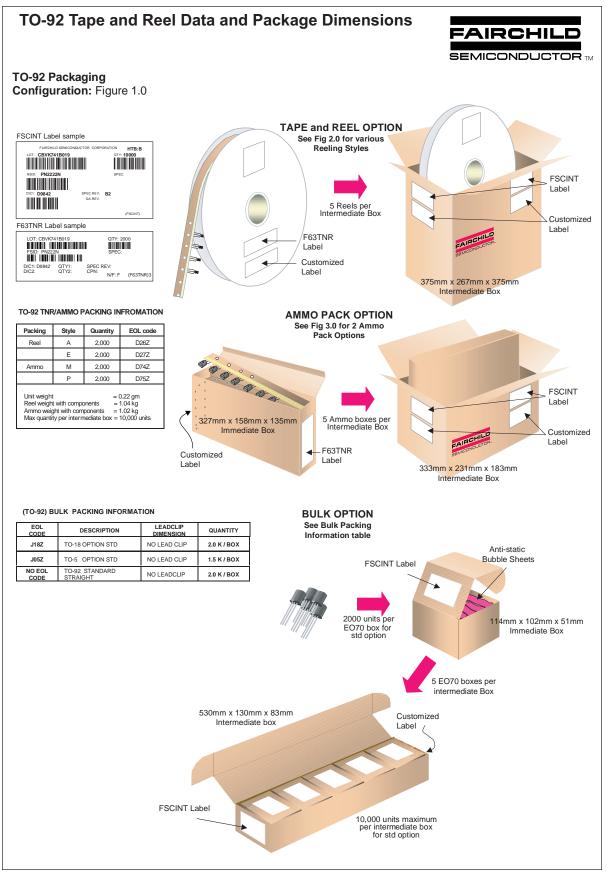
Typical Characteristics



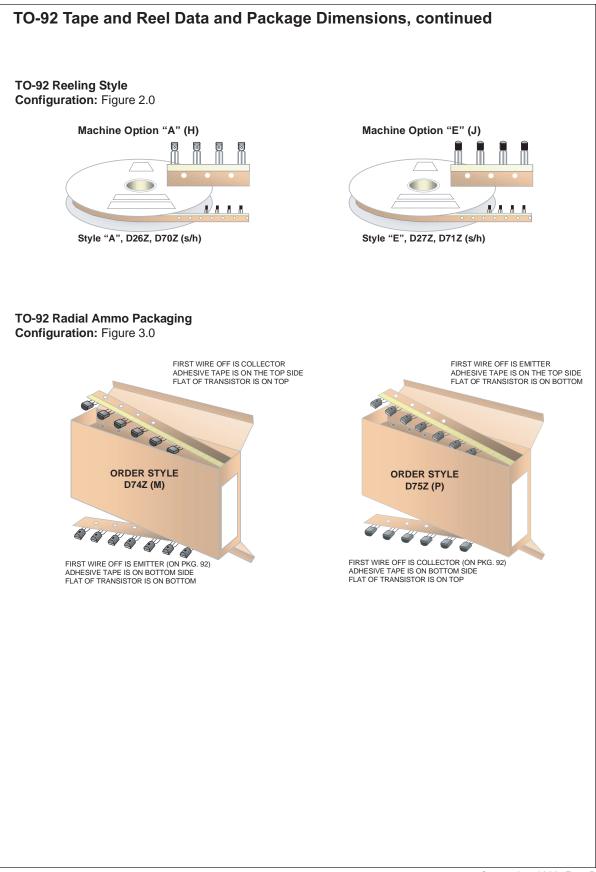


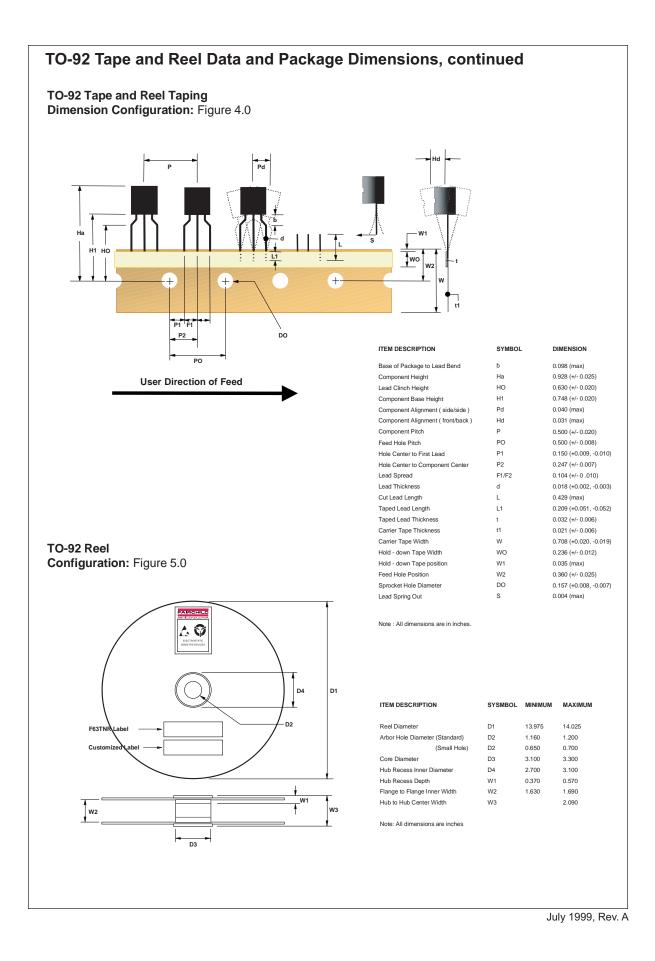


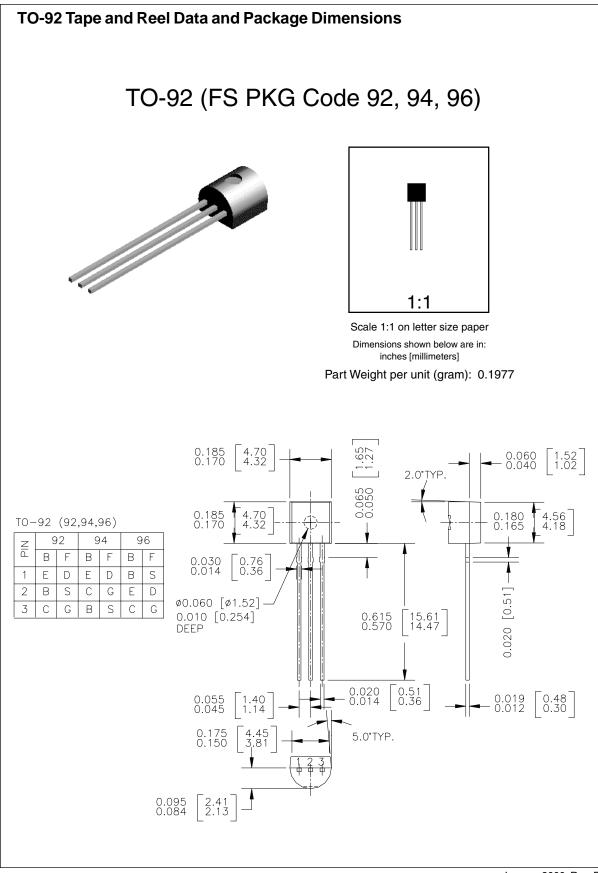
MPSA92 / MMBTA92 / PZTA92



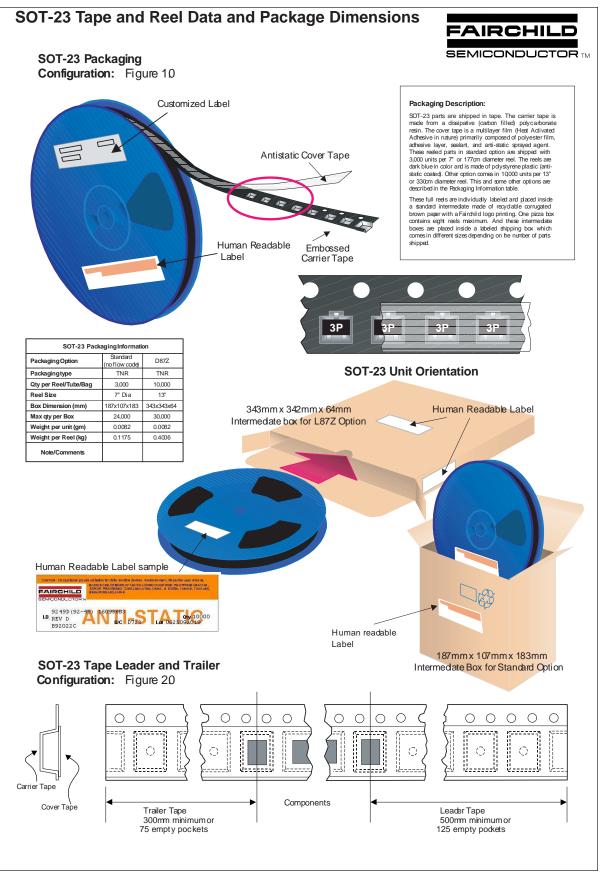
September 1999, Rev. B



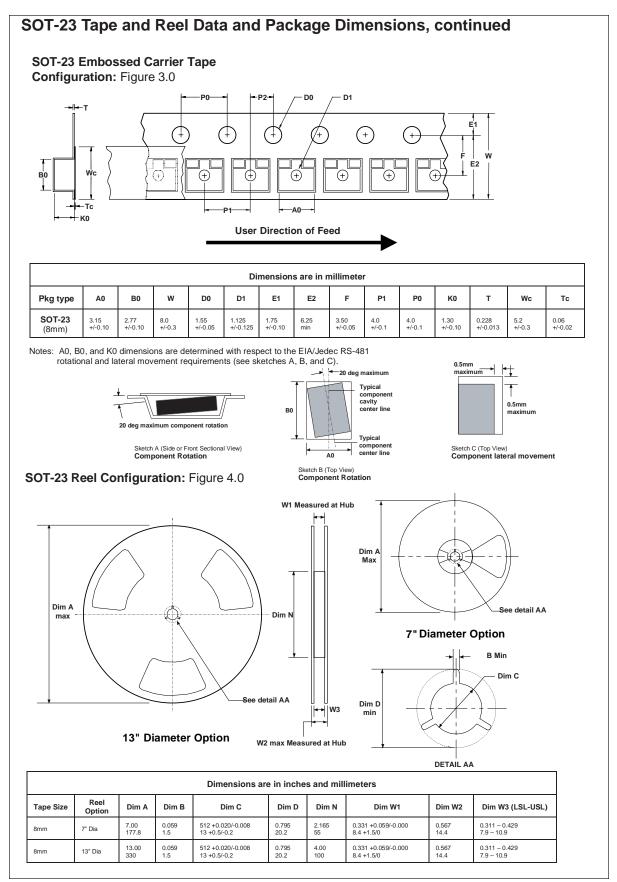




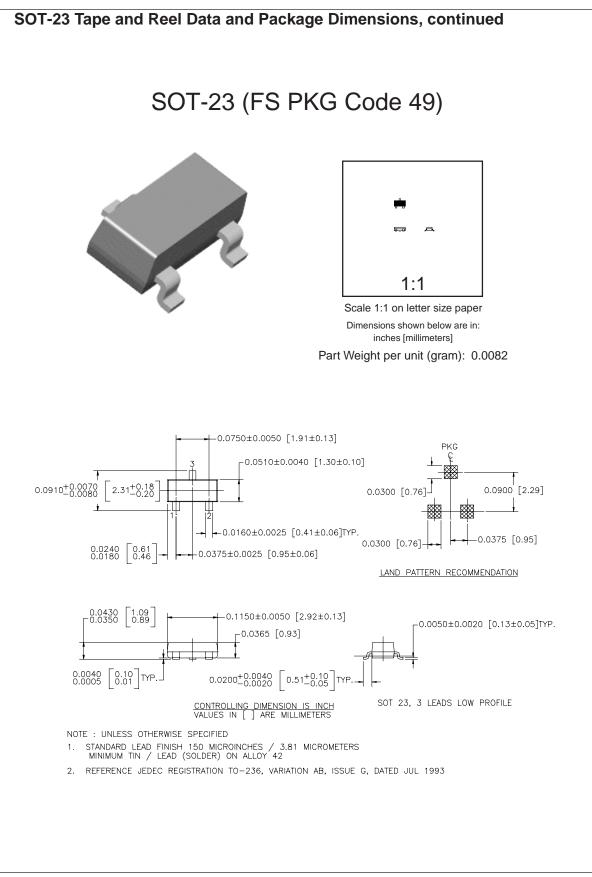
January 2000, Rev. B



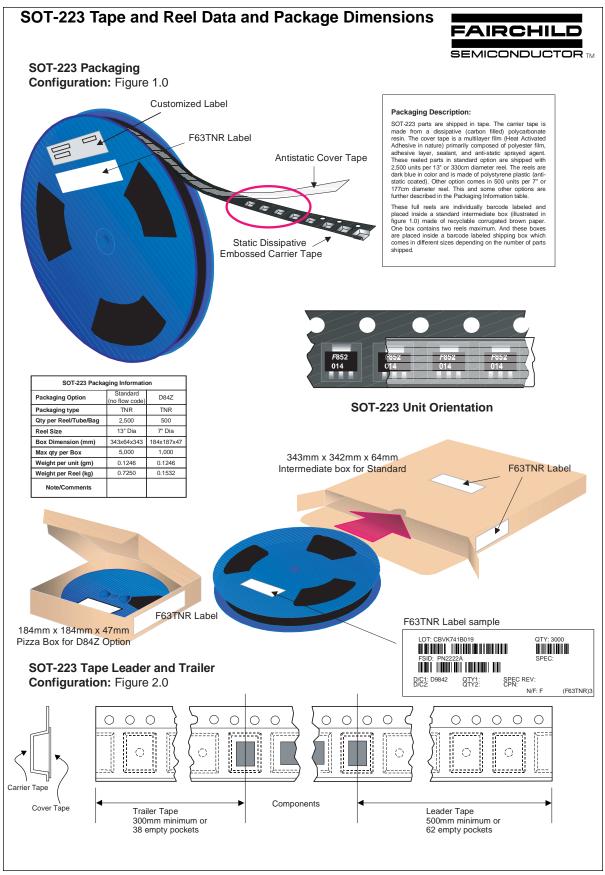
September 1999, Rev. C



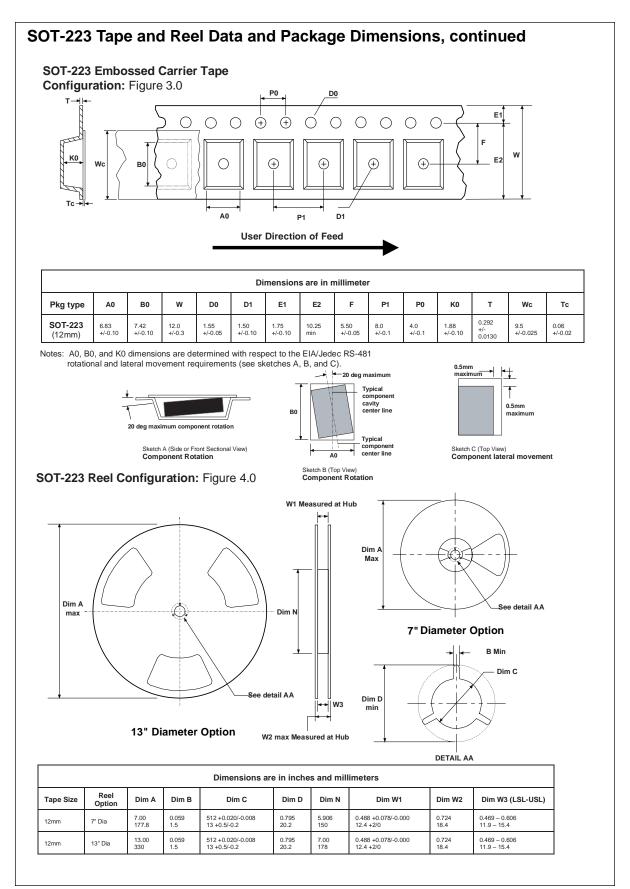
September 1999, Rev. C

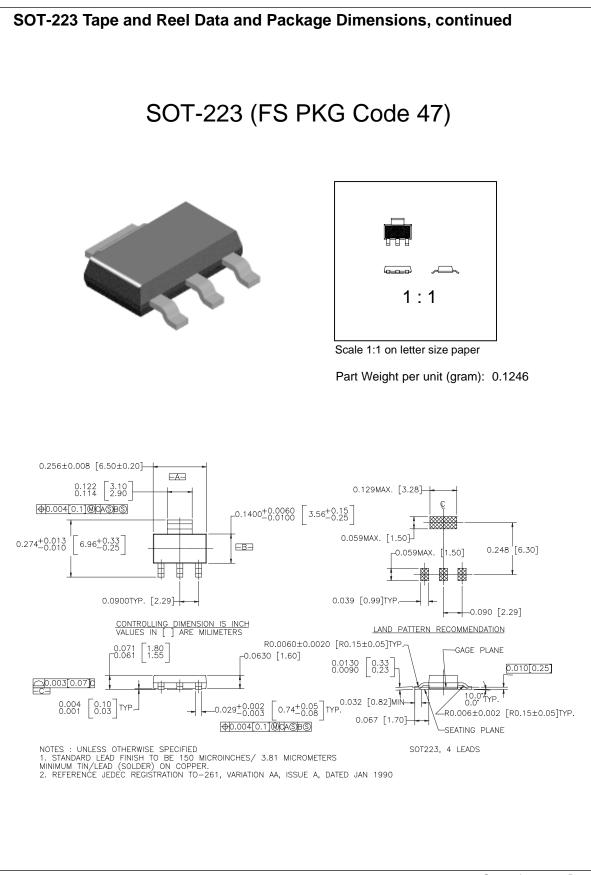


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September 1999, Rev. B





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PRODUCT STATUS DEFINITIONS

Definition of Terms

| Datasheet Identification | Product Status | Definition |
|--------------------------|---------------------------|---|
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